

Description

The VSM20N06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

N channel

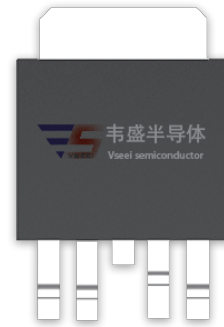
- $V_{DS} = 60V, I_D = 20A$
 $R_{DS(ON)} < 35m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 40m\Omega @ V_{GS} = 4.5V$

p channel

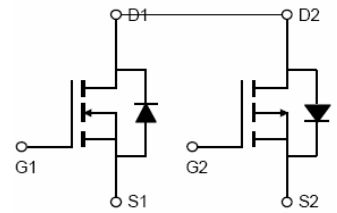
- $V_{DS} = -60V, I_D = -12A$
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 125m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- H-bridge
- Inverters



TO-252-4L



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM20N06-T2-4	VSM20N06	TO-252-4L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	60	-60	V
Gate-Source Voltage		V_{GS}	± 20	± 20	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	20	-12	A
	$T_C = 100^\circ C$		14	-8.5	
Pulsed Drain Current ^(Note 1)		I_{DM}	60	-30	A
Maximum Power Dissipation	$T_C = 25^\circ C$	P_D	50		W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 175		$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3	$^\circ C/W$
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N-Channel Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	24	35	mΩ
		V _{GS} =4.5V, I _D =20A		30	40	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5A	11	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	900	-	PF
Output Capacitance	C _{oss}		-	60	-	PF
Reverse Transfer Capacitance	C _{rss}		-	25	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =2A, R _L =6.7Ω V _{GS} =10V, R _G =3Ω	-	5	-	nS
Turn-on Rise Time	t _r		-	2.6	-	nS
Turn-Off Delay Time	t _{d(off)}		-	16.1	-	nS
Turn-Off Fall Time	t _f		-	2.3	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =4.5A, V _{GS} =10V	-	25	-	nC
Gate-Source Charge	Q _{gs}		-	4.5	-	nC
Gate-Drain Charge	Q _{gd}		-	6.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	20	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =20A di/dt = 100A/μs ^(Note3)	-	29	-	nS
Reverse Recovery Charge	Q _{rr}		-	49	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=30V$, $V_G=10V$, $L=0.5mH$, $R_g=25\Omega$

N-Channel Typical Electrical and Thermal Characteristics (Curves)

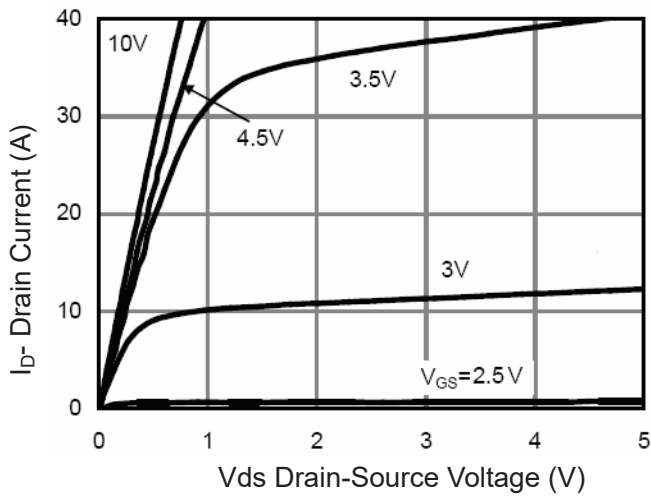


Figure 1 Output Characteristics

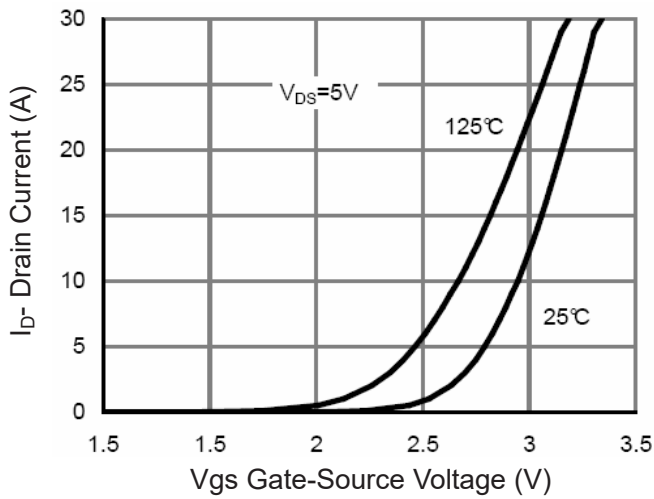


Figure 2 Transfer Characteristics

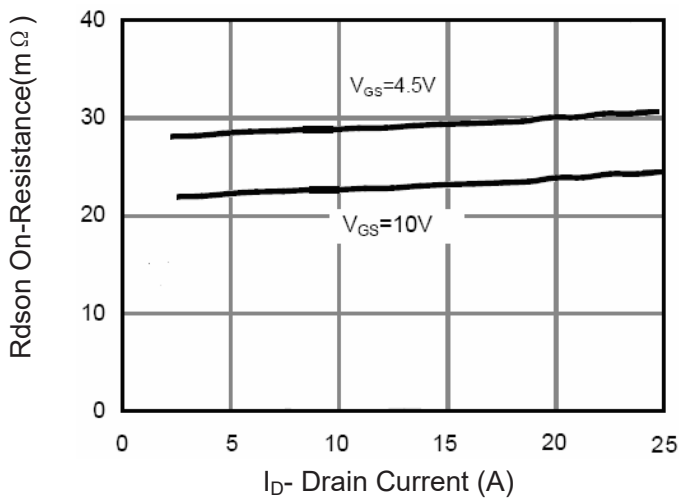


Figure 3 Rdson- Drain Current

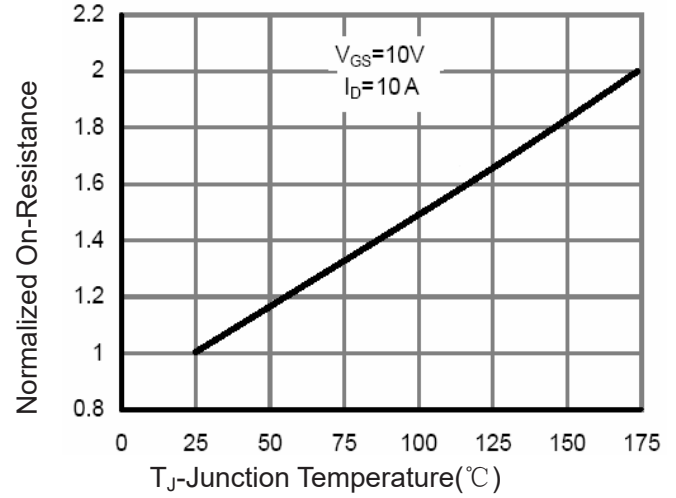


Figure 4 Rdson-Junction Temperature

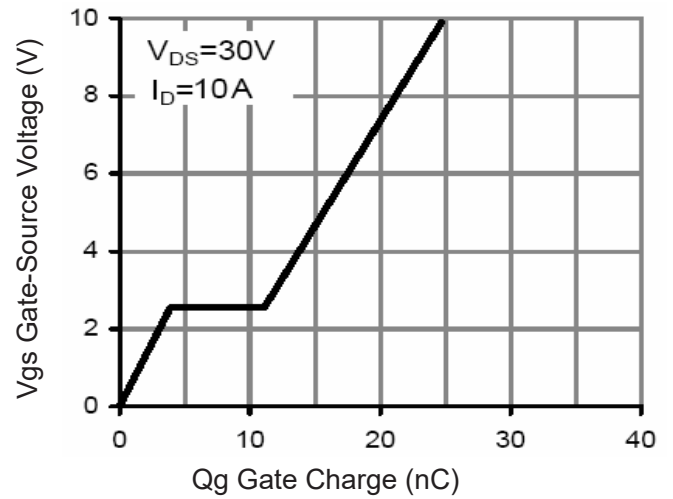


Figure 5 Gate Charge

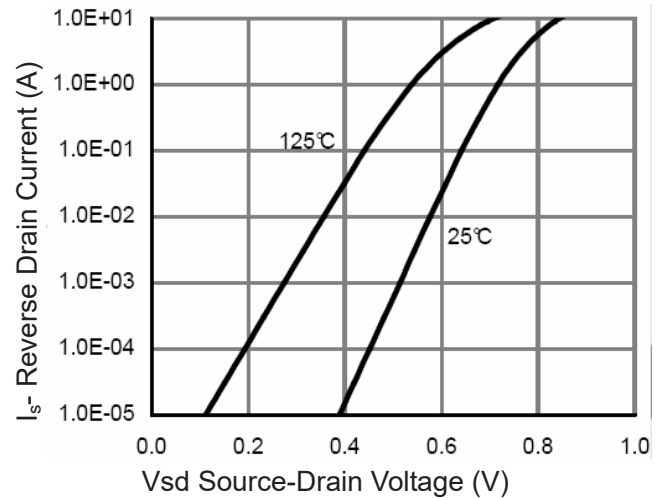
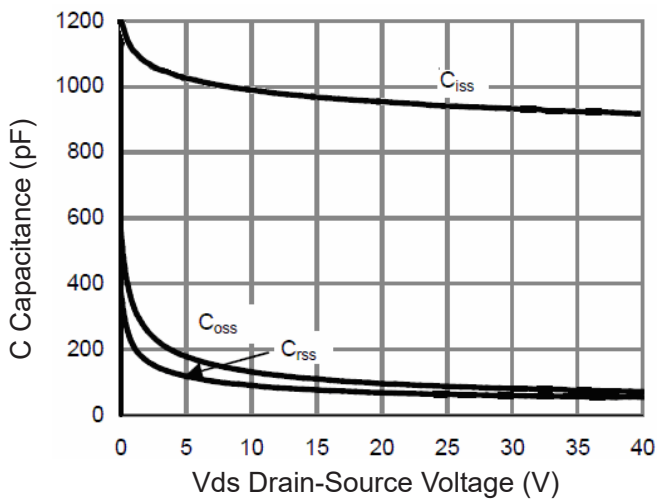
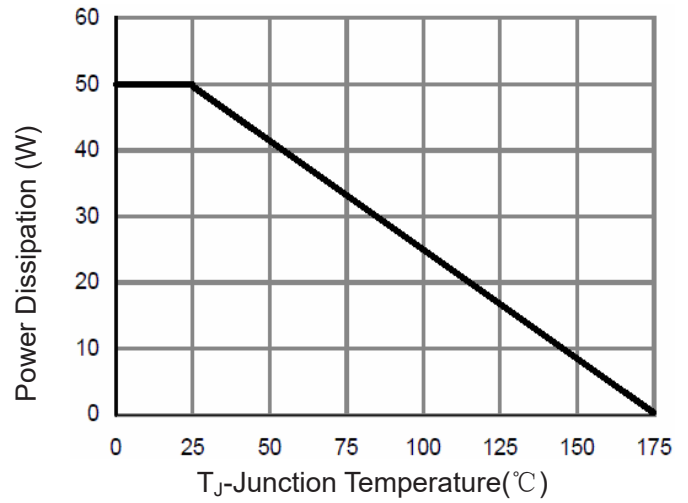
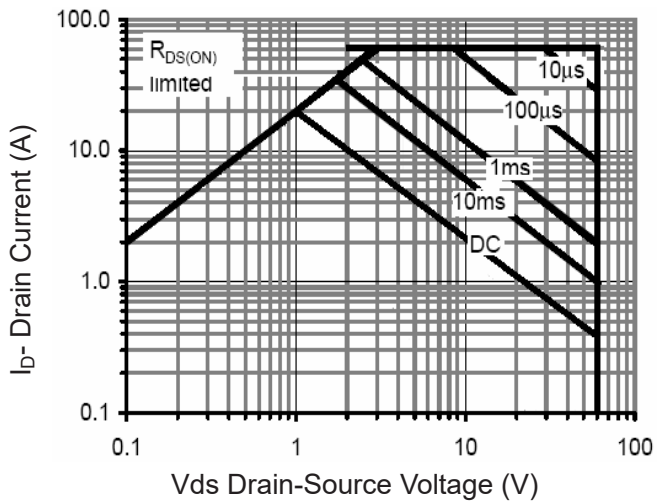
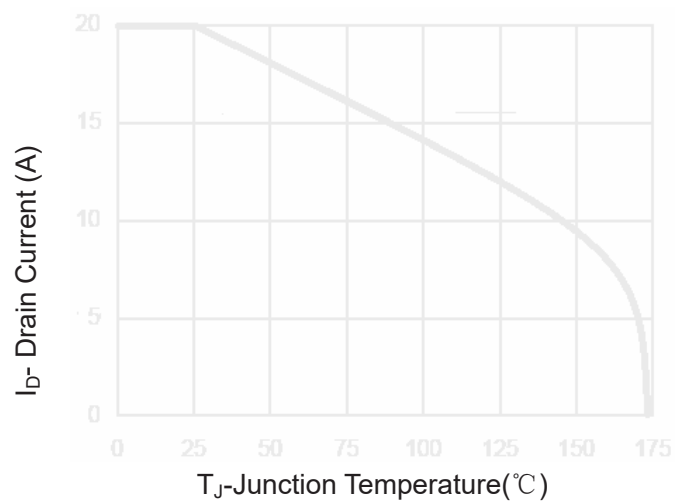
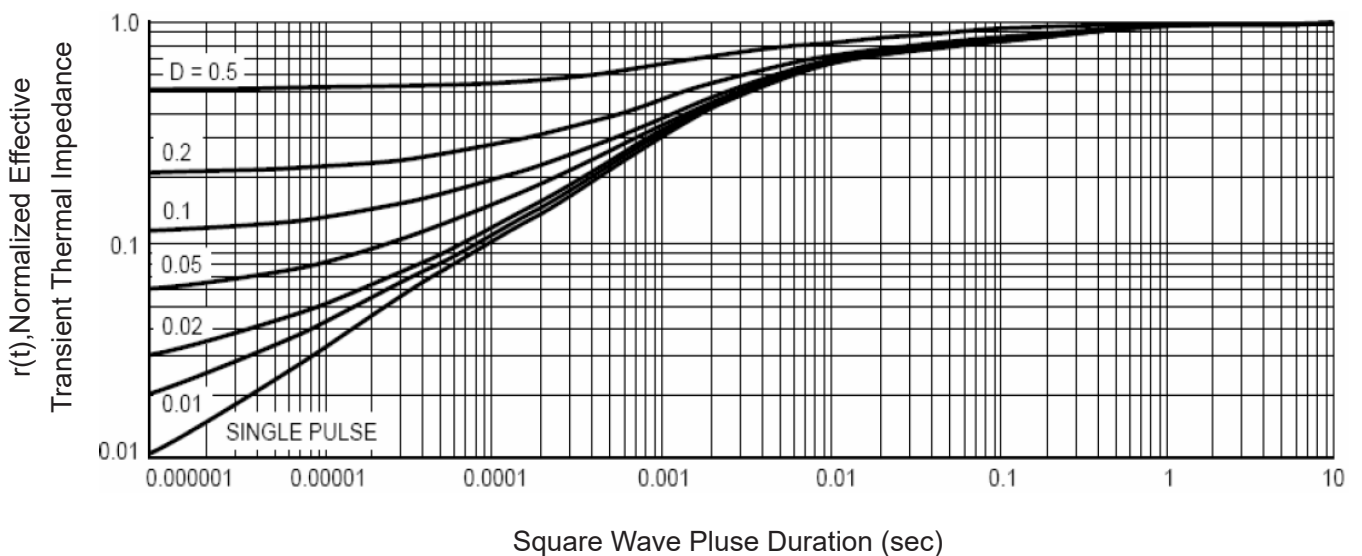


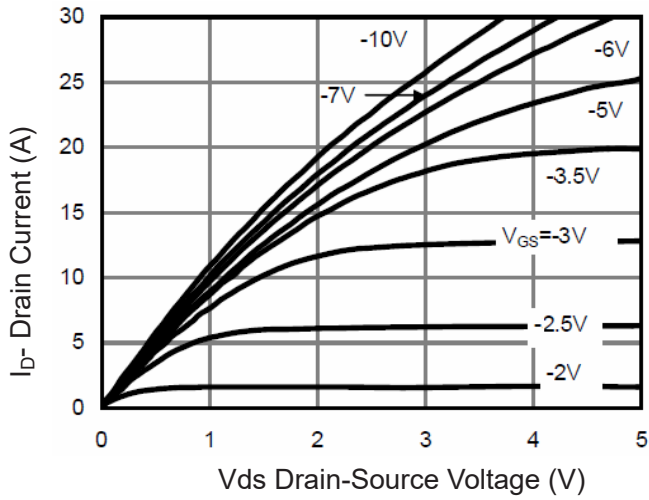
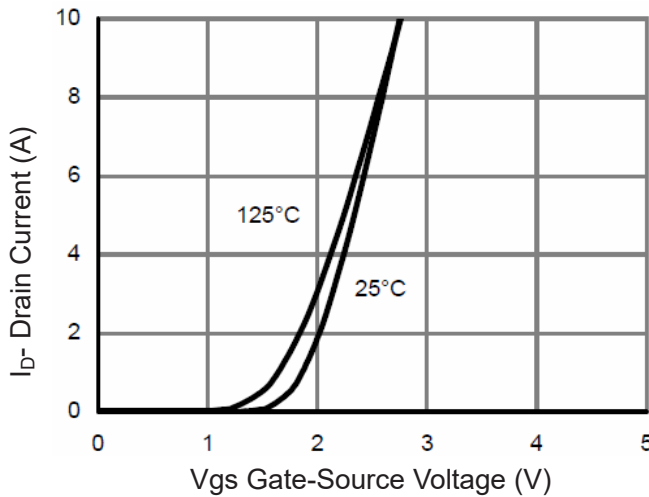
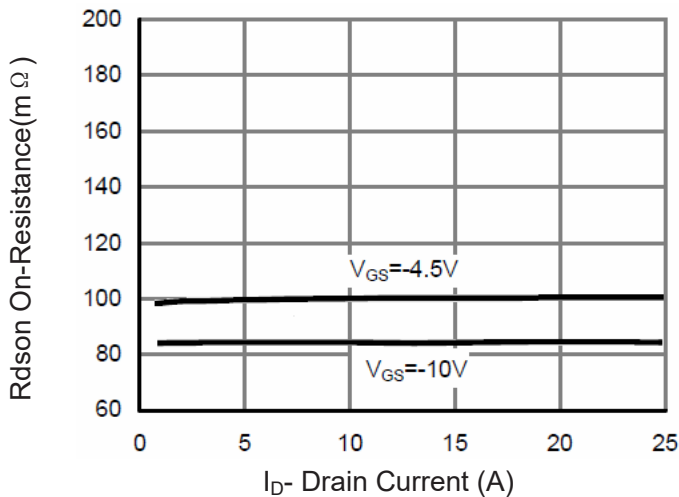
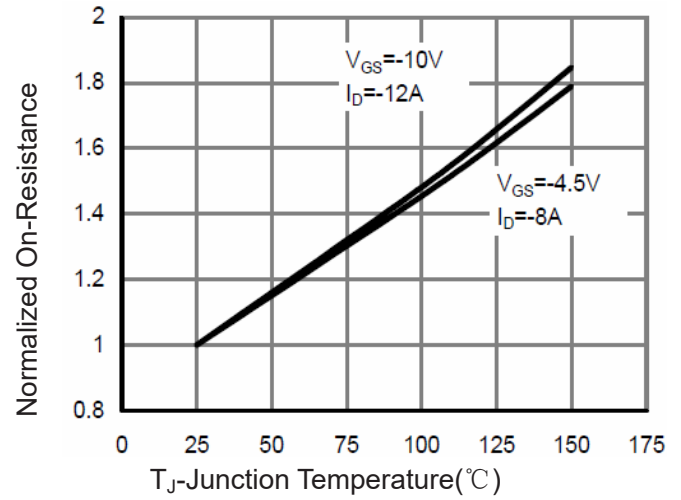
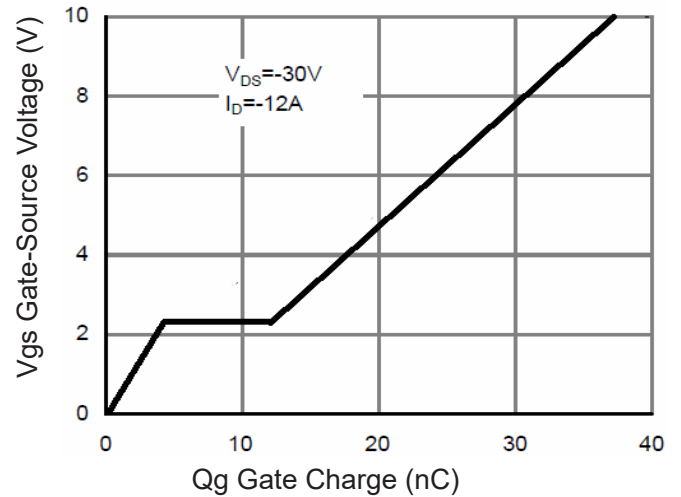
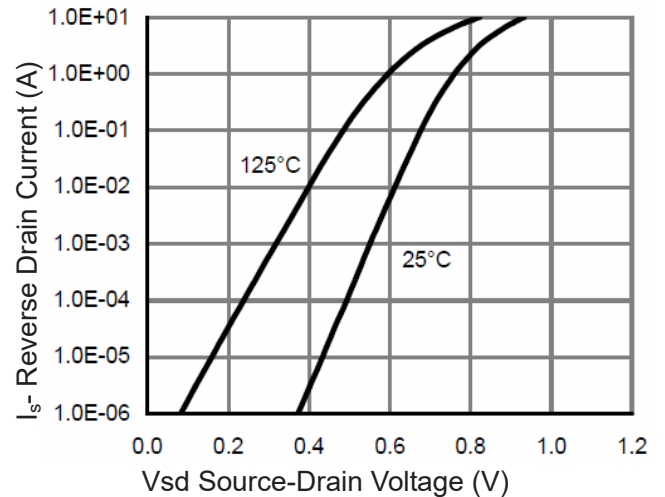
Figure 6 Source- Drain Diode Forward

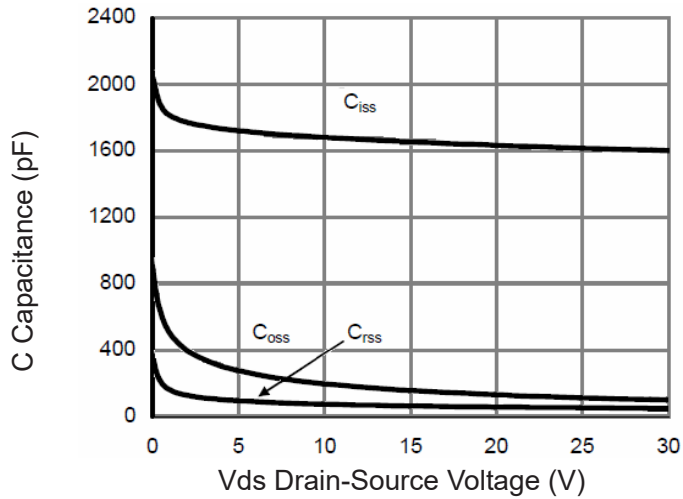
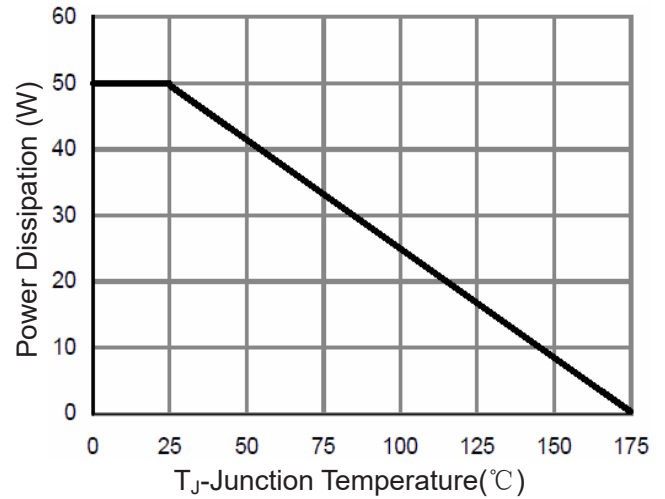
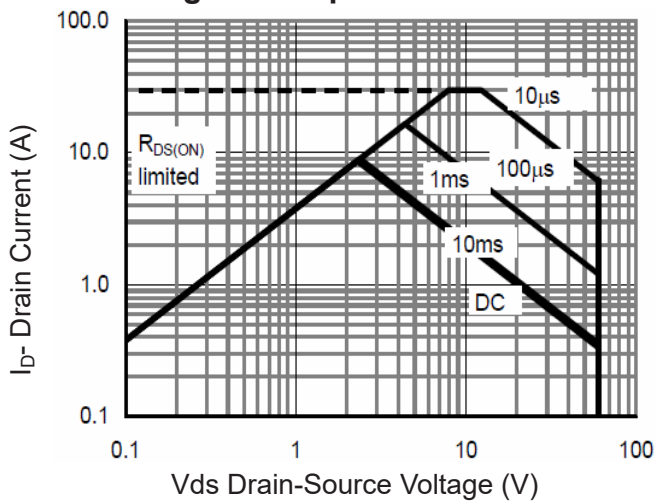
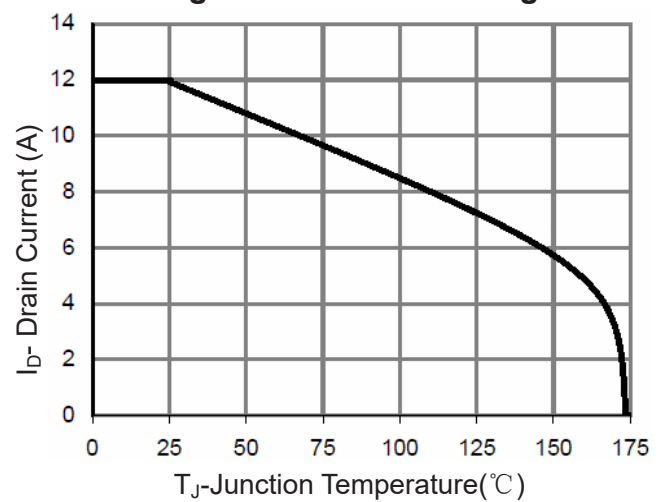
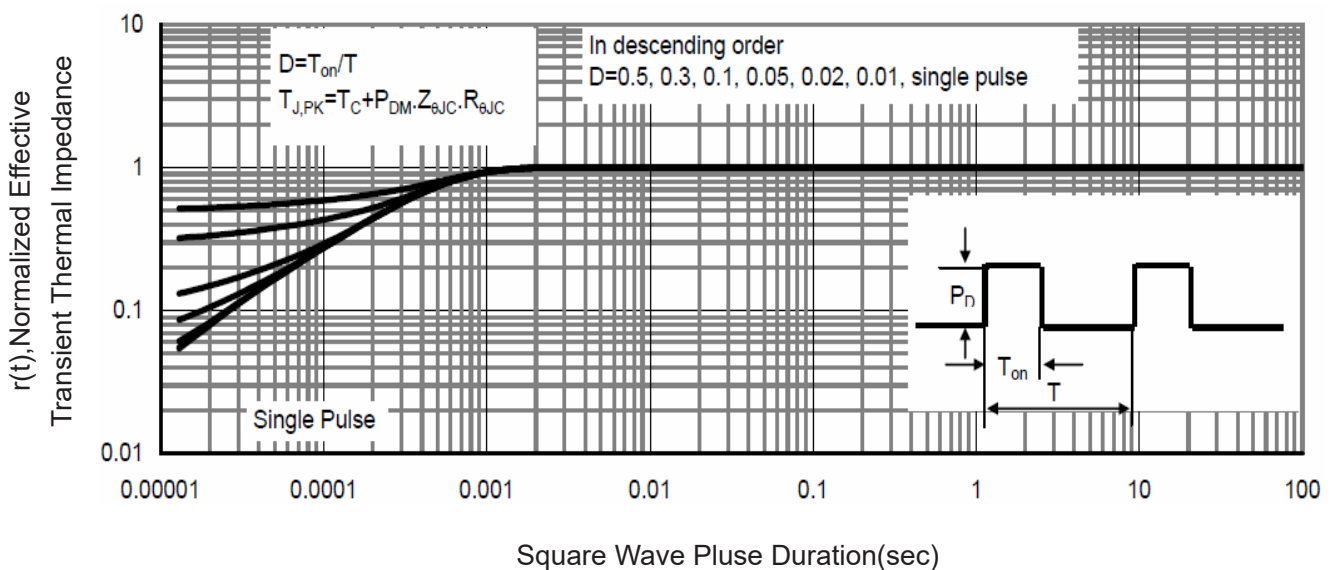

Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 ID Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1	-1.5	-2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-12A	-	84	100	mΩ
		V _{GS} =-4.5V, I _D =-8A	-	100	125	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-12A	-	10	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	1630.7	-	PF
Output Capacitance	C _{oss}		-	90.6	-	PF
Reverse Transfer Capacitance	C _{rss}		-	77.3	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =1.5Ω, V _{GS} =-10V, R _G =3Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	33	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-12A, V _{GS} =-10V	-	37.6		nC
Gate-Source Charge	Q _{gs}		-	4.3		nC
Gate-Drain Charge	Q _{gd}		-	7.2		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =-12A	-		-1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	-12	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 12A di/dt = -100A/μs ^(Note3)	-	35		nS
Reverse Recovery Charge	Q _{rr}		-	38		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

P-Channel Typical Electrical and Thermal Characteristics (Curves)


Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

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